

HYG170C03LR1C2

30V Complementary MOSFET

Feature

N- Channel

$V_{ds} = 30V$

20 A ($V_{gs} = 10V$)

15 m Ω ($V_{gs} = 10V$)

22 m Ω ($V_{gs} = 4.5V$)

P - Channel

$V_{ds} = -30V$

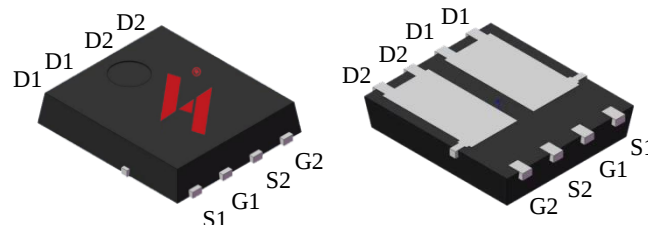
- 19 A ($V_{gs} = -10V$)

22 m Ω ($V_{gs} = -10V$)

40 m Ω ($V_{gs} = -4.5V$)

- 100% Avalanche Tested
- Reliable and Rugged
- Halogen Free and Green Devices Available (RoHS Compliant)

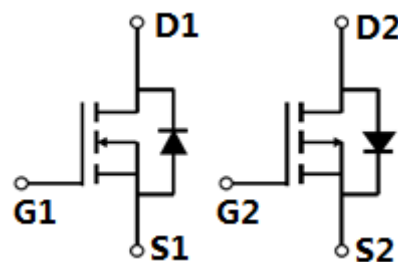
Pin Description



PDFN5*6-8L

Applications

- Synchronous Rectifiers
- Wireless Power
- H-bridge Motor Drive



N-Channel

P-Channel

Ordering and Marking Information

 C2 G170C03 XYMXXXXXX	Package Code C2: PDFN5*6-8L Date Code XYMXXXXXX
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Note: HUAYI lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish, which are fully compliant with RoHS. HUAYI lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020 for MSL classification at lead-free peak reflow temperature. HUAYI defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

HUAYI reserves the right to make changes, corrections, enhancements, modifications, and improvements to this product and/or to this document at any time without notice.

Absolute Maximum Ratings

Symbol	Parameter		N- Channel	P- Channel	Unit
	Common Ratings (Tc=25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		30	-30	V
V _{GSS}	Gate-Source Voltage		±20		V
T _J	Junction Temperature Range		-55 to 175		°C
T _{STG}	Storage Temperature Range		-55 to 175		°C
I _S	Source Current-Continuous(Body)	Tc=25°C	20	-19	A
	Mounted on Large Heat Sink				
I _{DM}	Pulsed Drain Current *	Tc=25°C	60	-60	A
I _D	Continuous Drain Current	Tc=25°C	20	-19	A
		Tc=100°C	14	-13.5	A
P _D	Maximum Power Dissipation	Tc=25°C	18.7	25	W
		Tc=100°C	9.3	12.5	W
R _{θJC}	Thermal Resistance, Junction-to-Ambient		8	6	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient		50	50	°C/W
E _{AS}	SinglePulsed-Avalanche Energy **	L=0.3mH	16.9	55	mJ

Note: * Repetitive rating; pulse width limited by max.junction temperature.

** Limited by TJmax , starting TJ=25°C, L = 0.3mH, RG= 25Ω, VGS =10V (N- Channel) /VGS =-10V (P- Channel) .

N-Mosfet Electrical Characteristics ($T_c = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG170C03LR1			Unit
			Min	Typ.	Max	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V,I _{DS} =250μA	30	-		V
I _{DSS}	Drain-to-Source LeakageCurrent	V _{DS} =30V,V _{GS} =0V	-	-	1	μA
			T _J =125°C	-	-	50
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1	1.8	3	V
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V,V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} *	Drain-Source On-State Resistance	V _{GS} =10V,I _{DS} =10A	-	15	19	mΩ
		V _{GS} =4.5V,I _{DS} =8A	-	22	28	
Diode Characteristics						
V _{SD} *	Diode Forward Voltage	I _{SD} =1A,V _{GS} =0V	-	0.75	1.0	V
t _{rr}	Reverse Recovery Time	I _{SD} =10A,dI _{SD} /dt=100A/μs	-	6	-	ns
Q _{rr}	Reverse Recovery Charge		-	2	-	nC

N-Mosfet Electrical Characteristics (Cont.) ($T_c = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG170C03LR1			Unit
			Min	Typ.	Max	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V, Frequency=1.0MHz	-	1.2	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, Frequency=1.0MHz	-	446	-	pF
C _{oss}	Output Capacitance		-	55.1	-	
C _{rss}	Reverse Transfer Capacitance		-	44.2	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V,R _G =2.5Ω, I _{DS} =10A,V _{GS} =10V	-	6	-	ns
T _r	Turn-on Rise Time		-	32	-	
t _{d(OFF)}	Turn-off Delay Time		-	11	-	
T _f	Turn-off Fall Time		-	2.7	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge (V _{GS} =10V,)	V _{DS} =24V,I _D =10A	-	9.2	-	nC
Q _g	Total Gate Charge (V _{GS} =4.5V)		-	4.6	-	
Q _{gs}	Gate-Source Charge		-	1.9	-	
Q _{gd}	Gate-Drain Charge		-	2.3	-	

Note: *Pulse test, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

N-Mosfet Typical Operating Characteristics

Figure 1: Power Dissipation

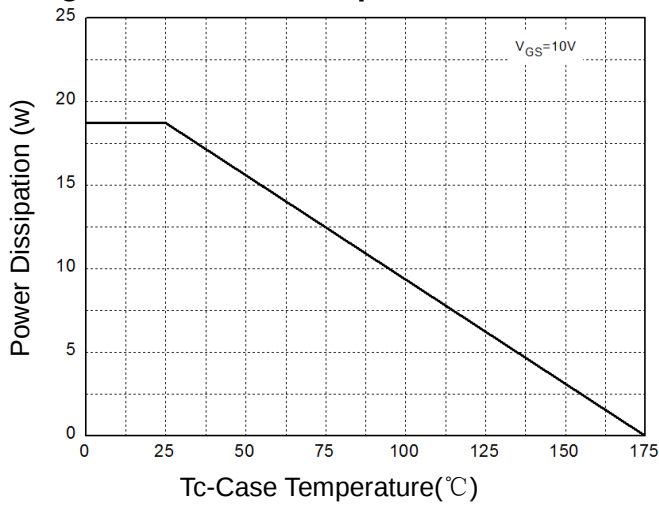


Figure 2: Drain Current

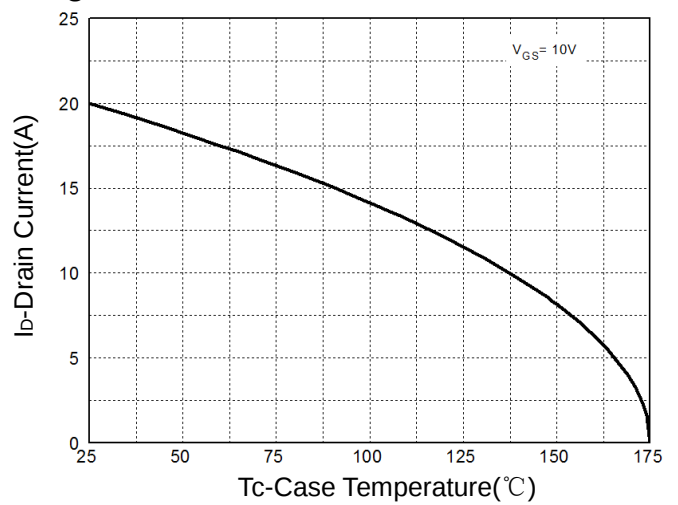


Figure 3: Safe Operation Area

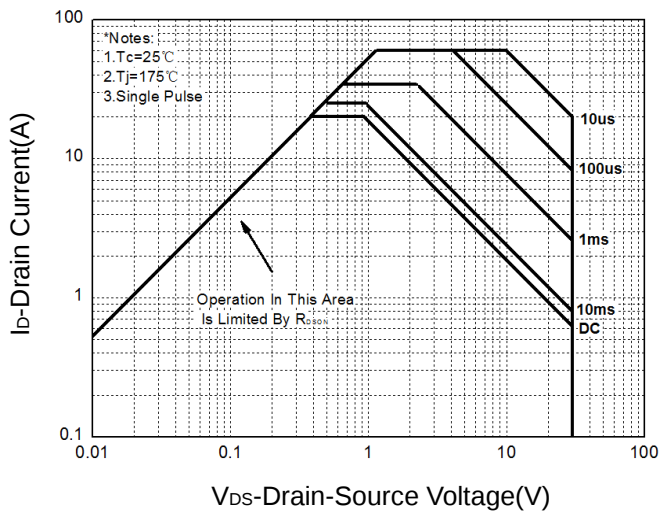


Figure 4: Thermal Transient Impedance

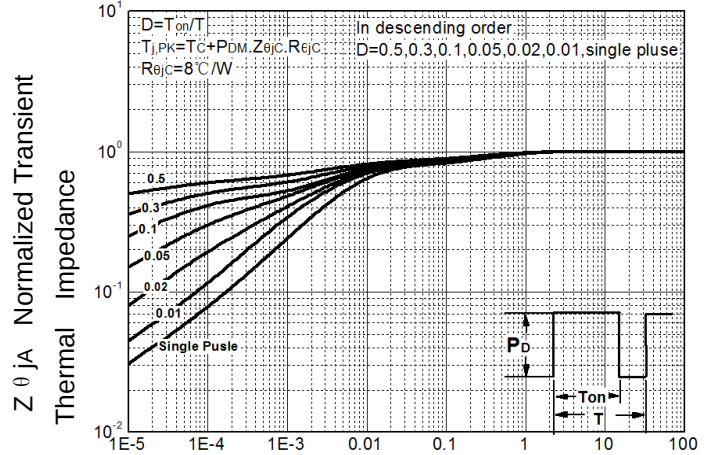


Figure 5: Output Characteristics

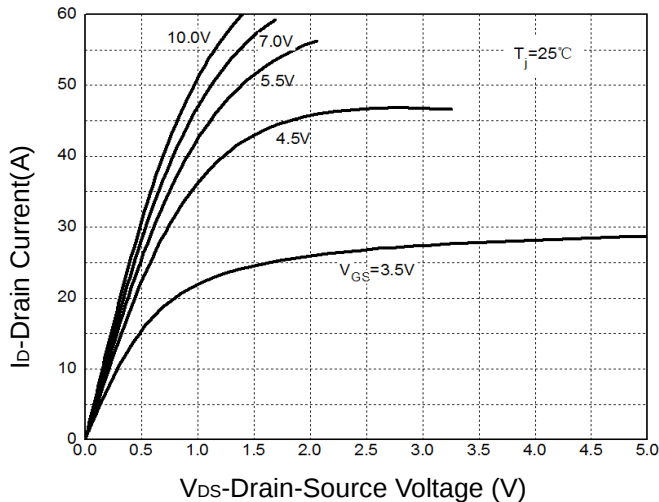
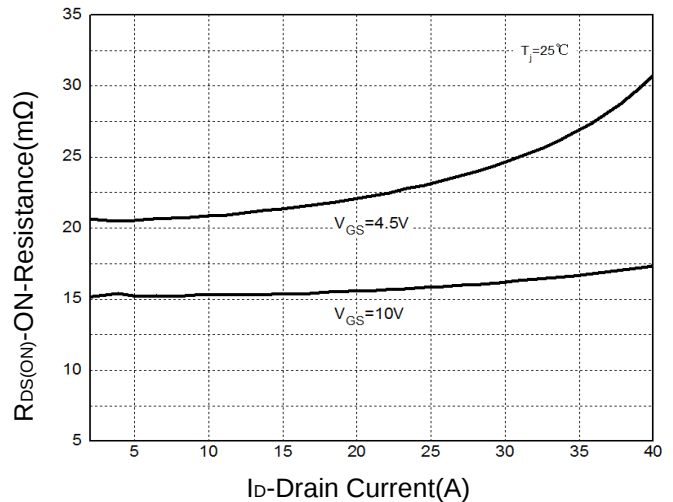


Figure 6: Drain-Source On Resistance



N-Mosfet Typical Operating Characteristics

Figure 7: On-Resistance vs. Temperature

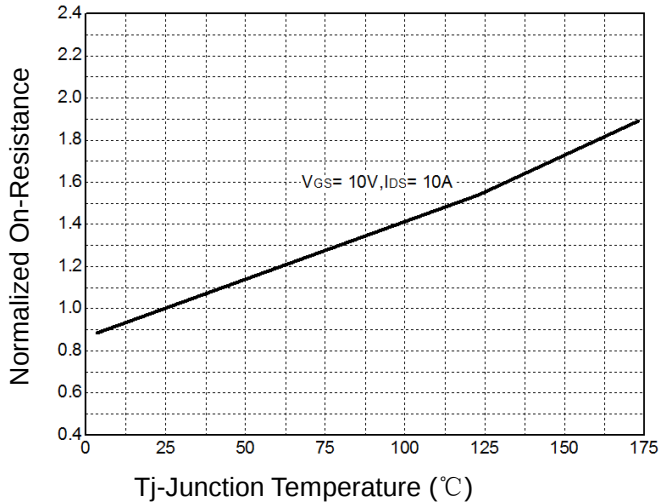


Figure 8: Source-Drain Diode Forward

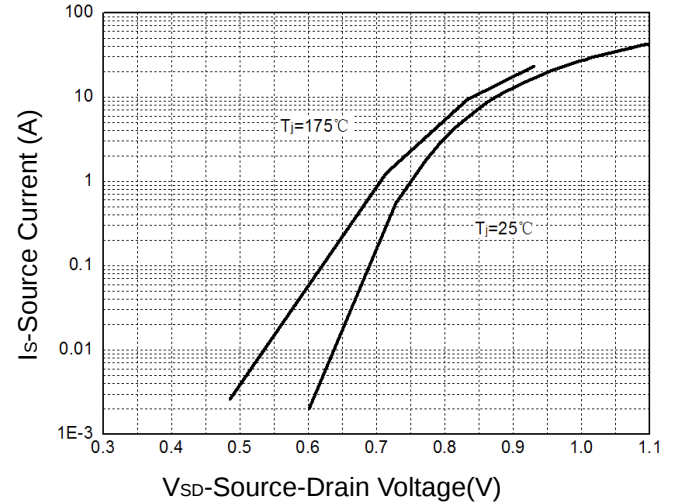


Figure 9: Capacitance Characteristics

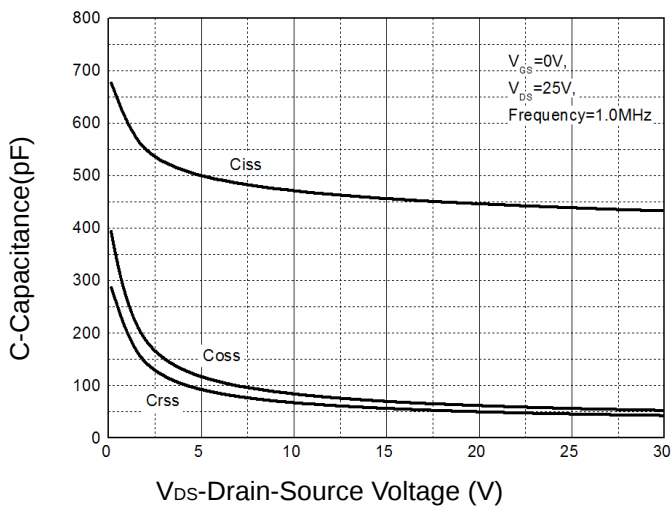
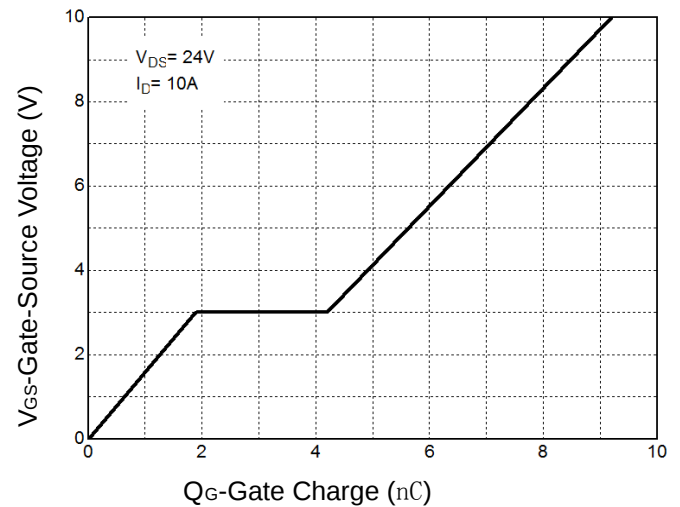
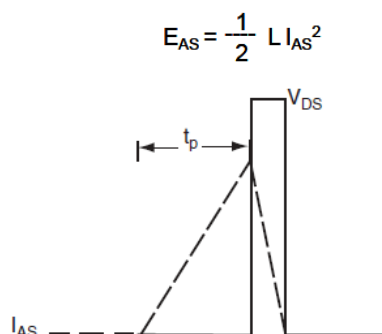
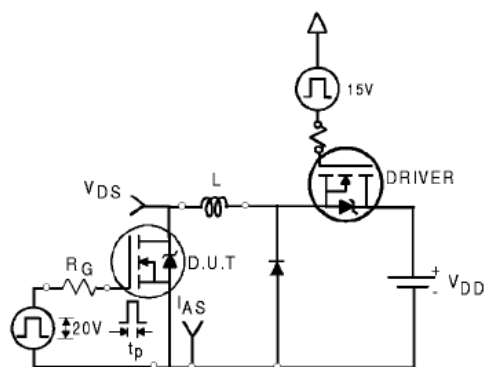


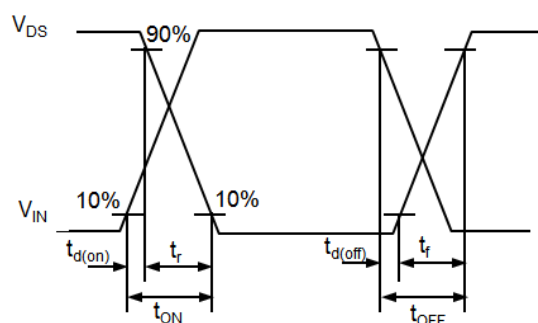
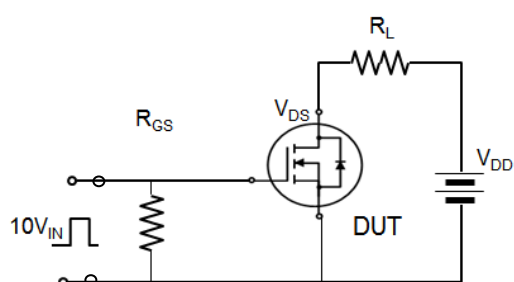
Figure 10: Gate Charge Characteristics



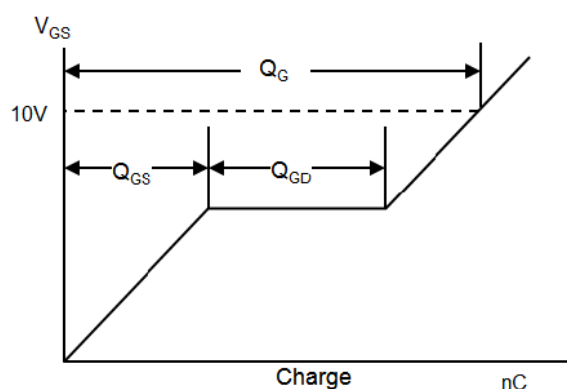
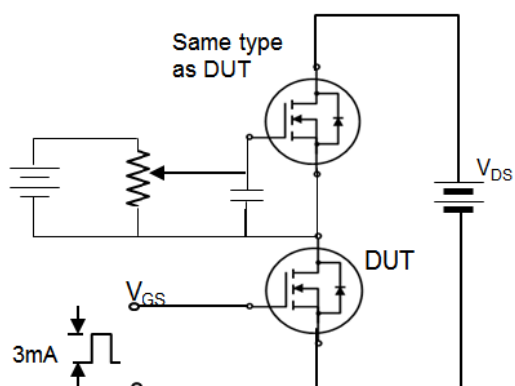
Avalanche Test Circuit



Switching Time Test Circuit



Gate Charge Test Circuit



P-Mosfet Electrical Characteristics ($T_c = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG170C03LR1			Unit
			Min	Typ.	Max	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	- 30	-		V
I _{DSS}	Drain-to-Source LeakageCurrent	V _{DS} =-30V, V _{GS} =0V	-	-	-1	μA
			T _J =125°C	-	-	-50
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1	-1.9	-3	V
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)*}	Drain-Source On-State Resistance	V _{GS} =-10V, I _{DS} =-10A	-	22	27	mΩ
		V _{GS} =-4.5V, I _{DS} =-6A		40	55	
Diode Characteristics						
V _{SD} *	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V	-	-0.75	-1	V
t _{rr}	Reverse Recovery Time	I _{SD} =-10A, dI _{SD} /dt=100A/μs	-	11	-	ns
Q _{rr}	Reverse Recovery Charge		-	4	-	nC

P-Mosfet Electrical Characteristics (Cont.) ($T_c = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG170C03LR1			Unit
			Min	Typ.	Max	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V, Frequency=1.0MHz	-	6	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-25V, Frequency=1.0MHz	-	1210	-	pF
C _{oss}	Output Capacitance		-	120	-	
C _{rss}	Reverse Transfer Capacitance		-	86	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-15V,R _G =2.5Ω, I _{DS} =-10A,V _{GS} =-10V	-	8	-	ns
T _r	Turn-on Rise Time		-	32	-	
t _{d(OFF)}	Turn-off Delay Time		-	25	-	
T _f	Turn-off Fall Time		-	28	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge(VGS= -10V)	V _{DS} =-24V, I _D =-10A	-	21	-	nC
Q _g	Total Gate Charge(VGS= -4.5V)		-	13	-	
Q _{gs}	Gate-Source Charge		-	6.1	-	
Q _{gd}	Gate-Drain Charge		-	3.8	-	

Note: *Pulse test, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

P-Mosfet Typical Operating Characteristics

Figure 1: Power Dissipation

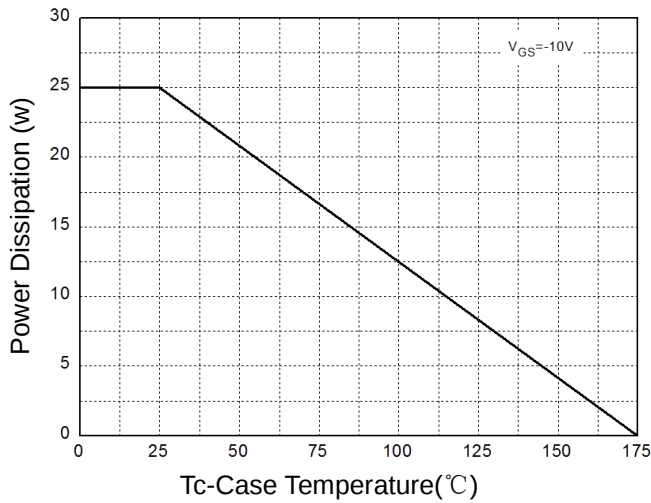


Figure 2: Drain Current

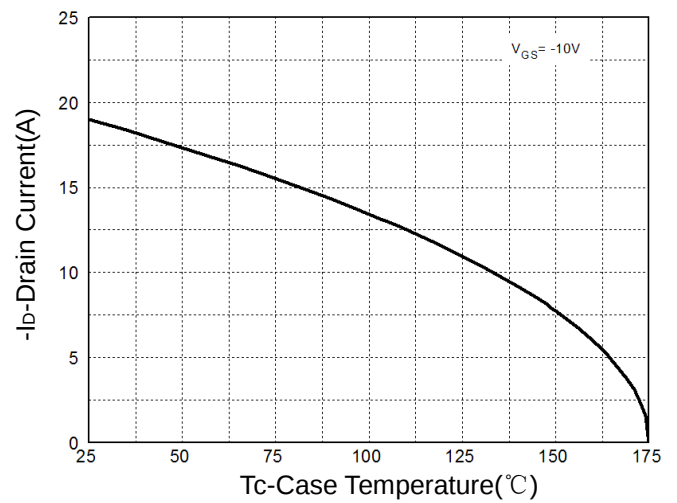


Figure 3: Safe Operation Area

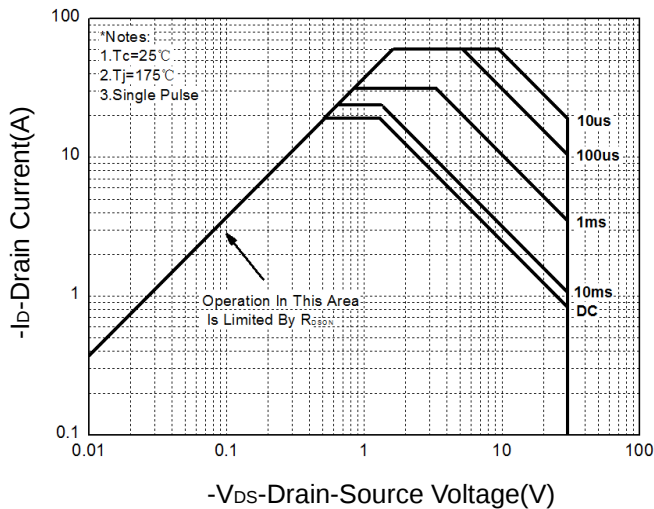


Figure 4: Thermal Transient Impedance

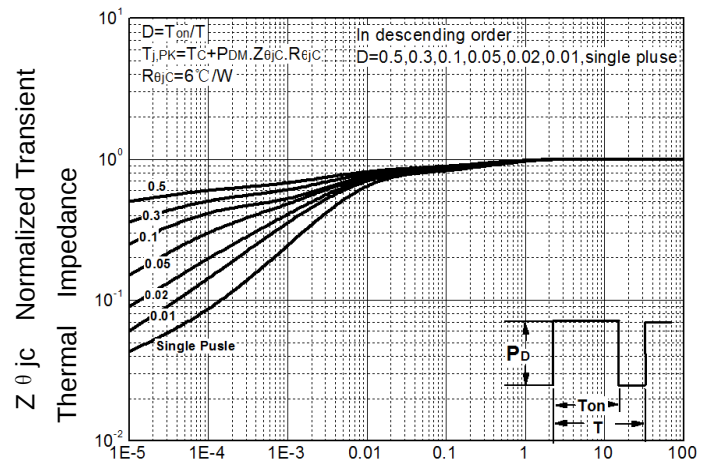


Figure 5: Output Characteristics

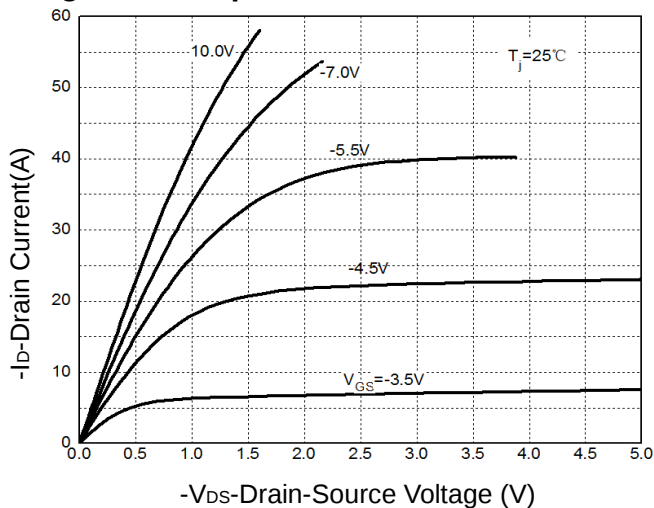
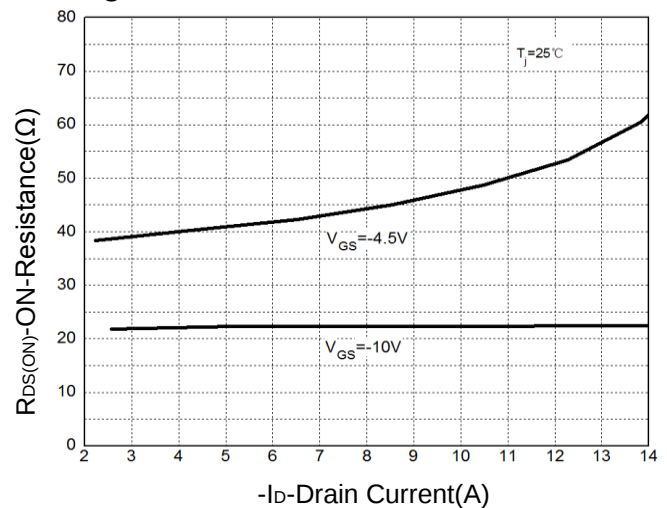


Figure 6: Drain-Source On Resistance



P-Mosfet Typical Operating Characteristics

Figure 7: On-Resistance vs. Temperature

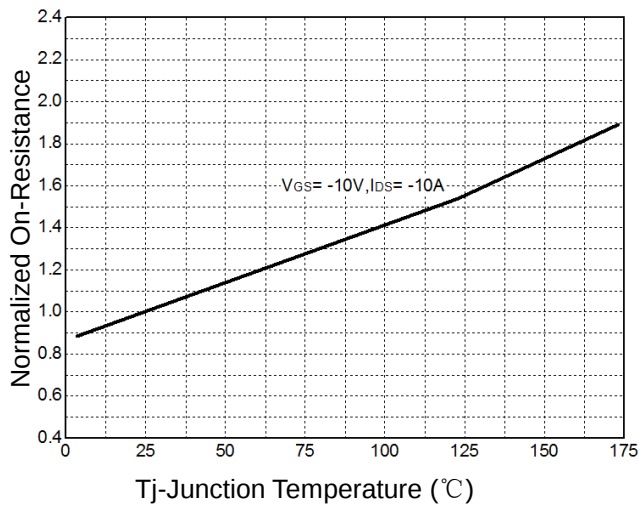


Figure 8: Source-Drain Diode Forward

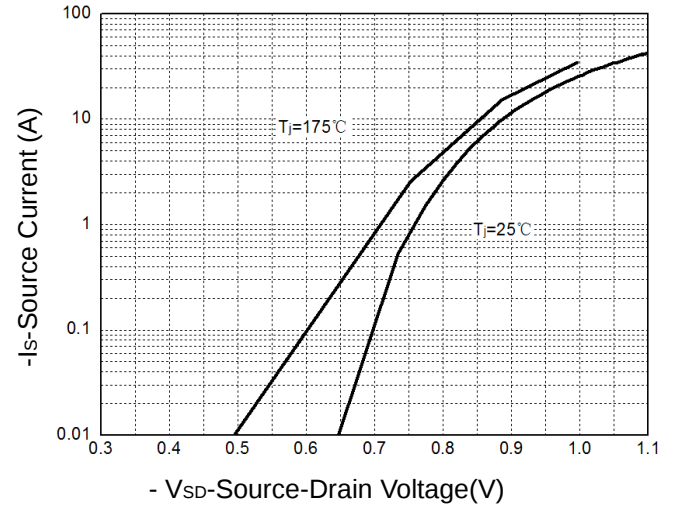


Figure 9: Capacitance Characteristics

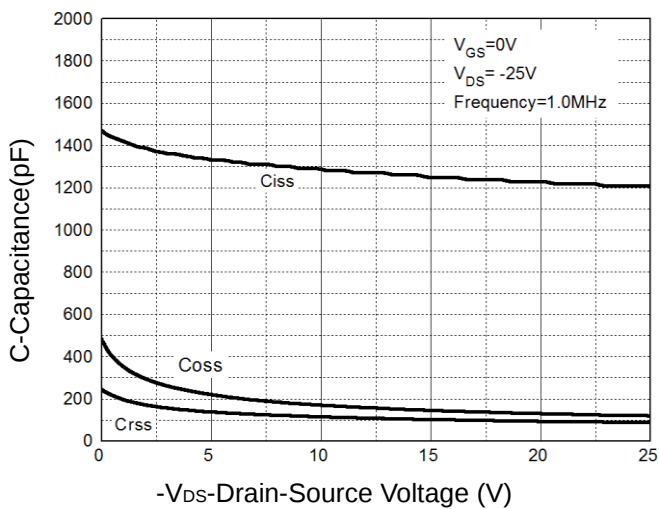
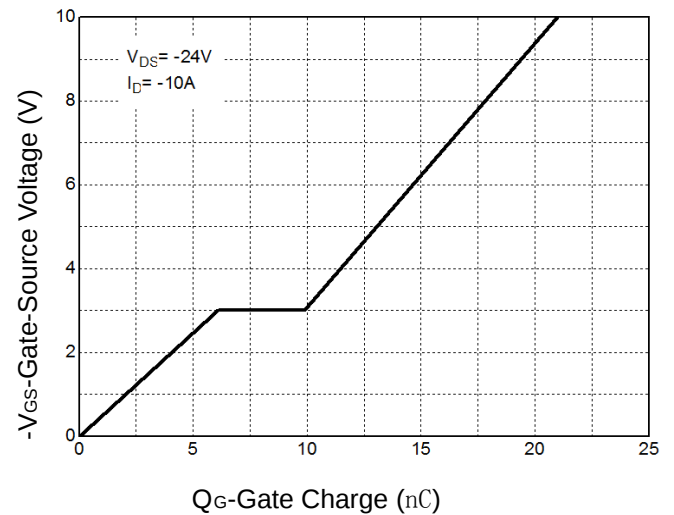
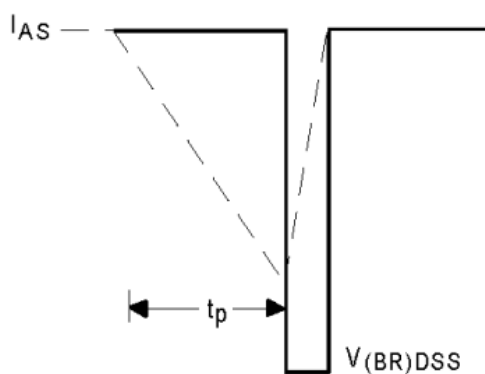
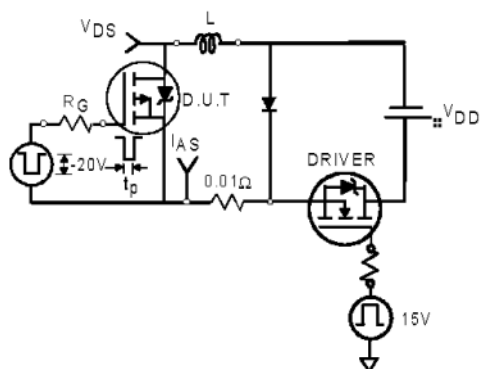


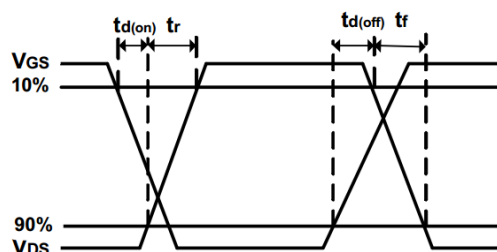
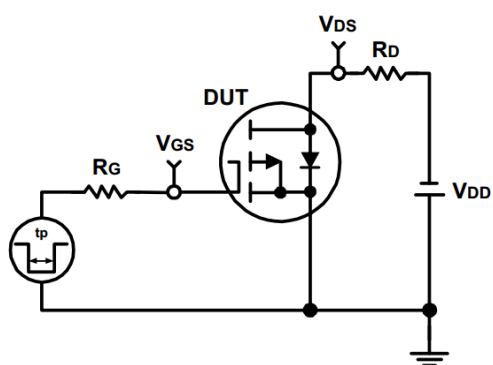
Figure 10: Gate Charge Characteristics



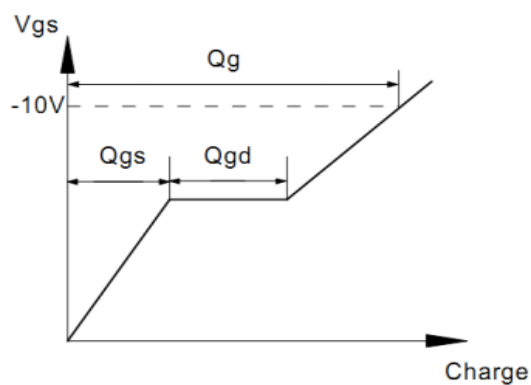
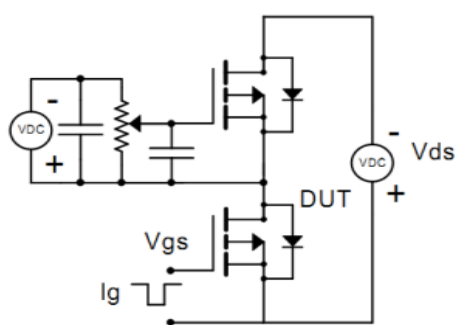
Avalanche Test Circuit



Switching Time Test Circuit



Gate Charge Test Circuit



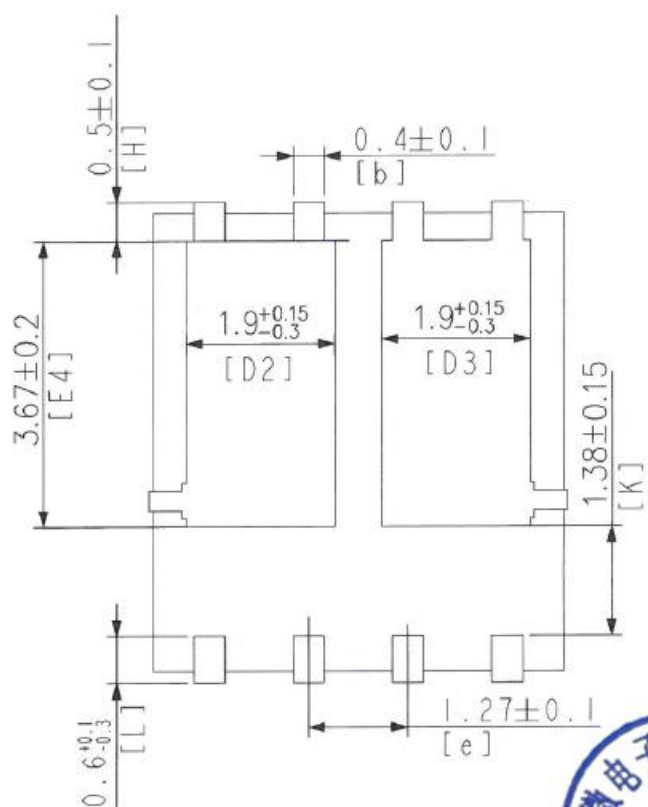
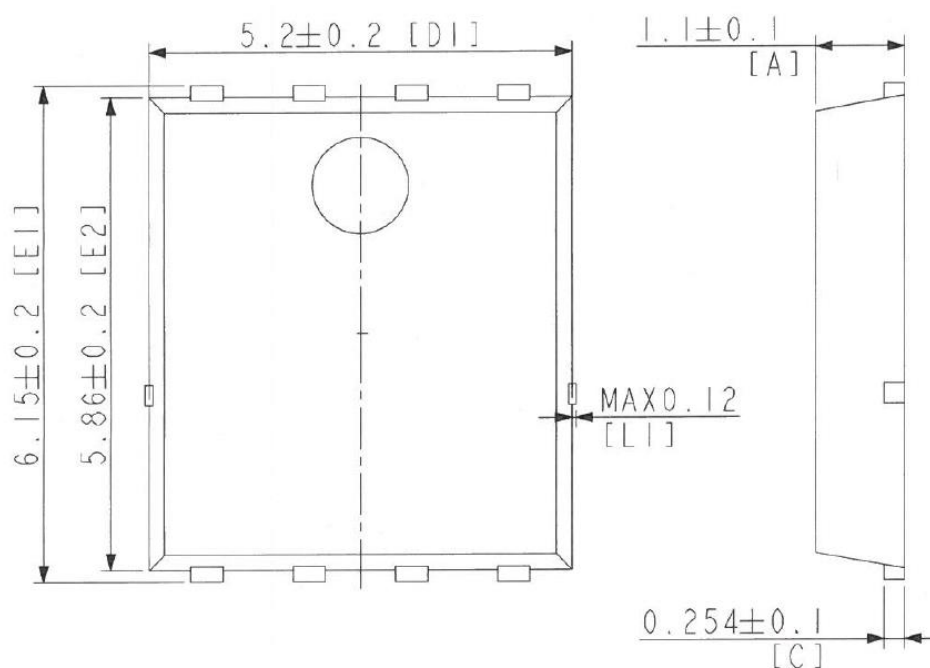
HYG170C03LR1C2

Device Per Unit

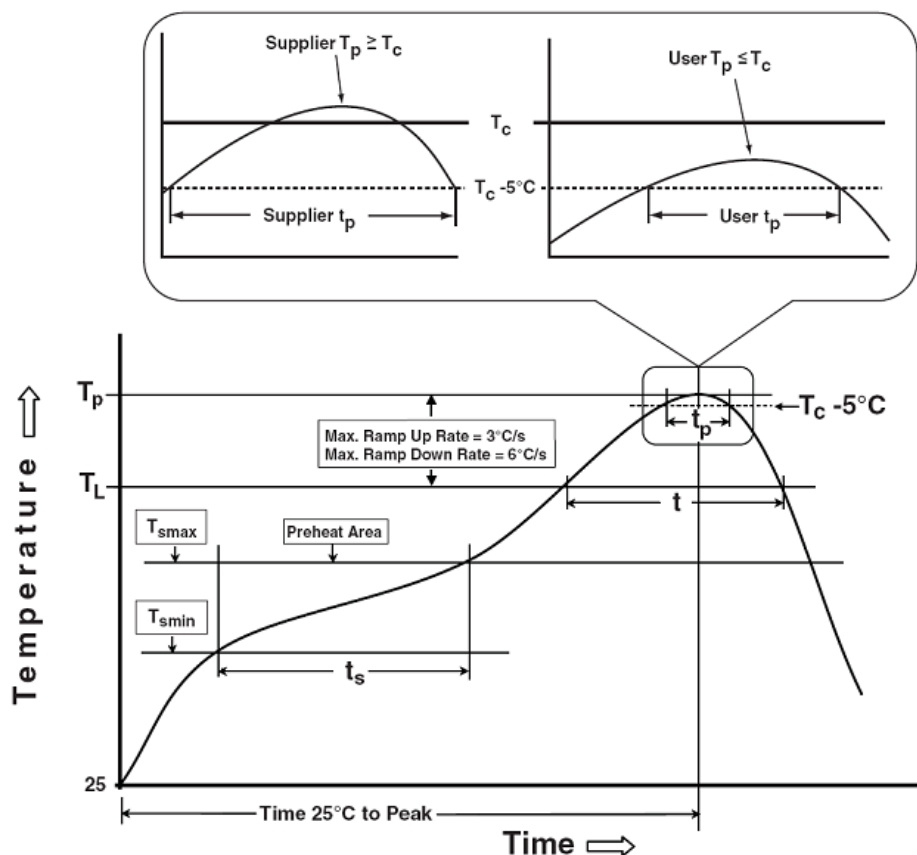
Package Type	Unit	Quantity
PDFN5*6-8L	Reel	5000

Package Information

PDFN5*6-8L



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
*Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1.SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2.Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ ≥2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	168 Hrs \ 500Hrs\ 1000 Hrs, Bias @ 125°C
HTRB	JESD-22, A108	168 Hrs \ 500Hrs\ 1000 Hrs, Bias @ 125°C
PCT	JESD-22, A102	96 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -55°C~150°C

Customer Service

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